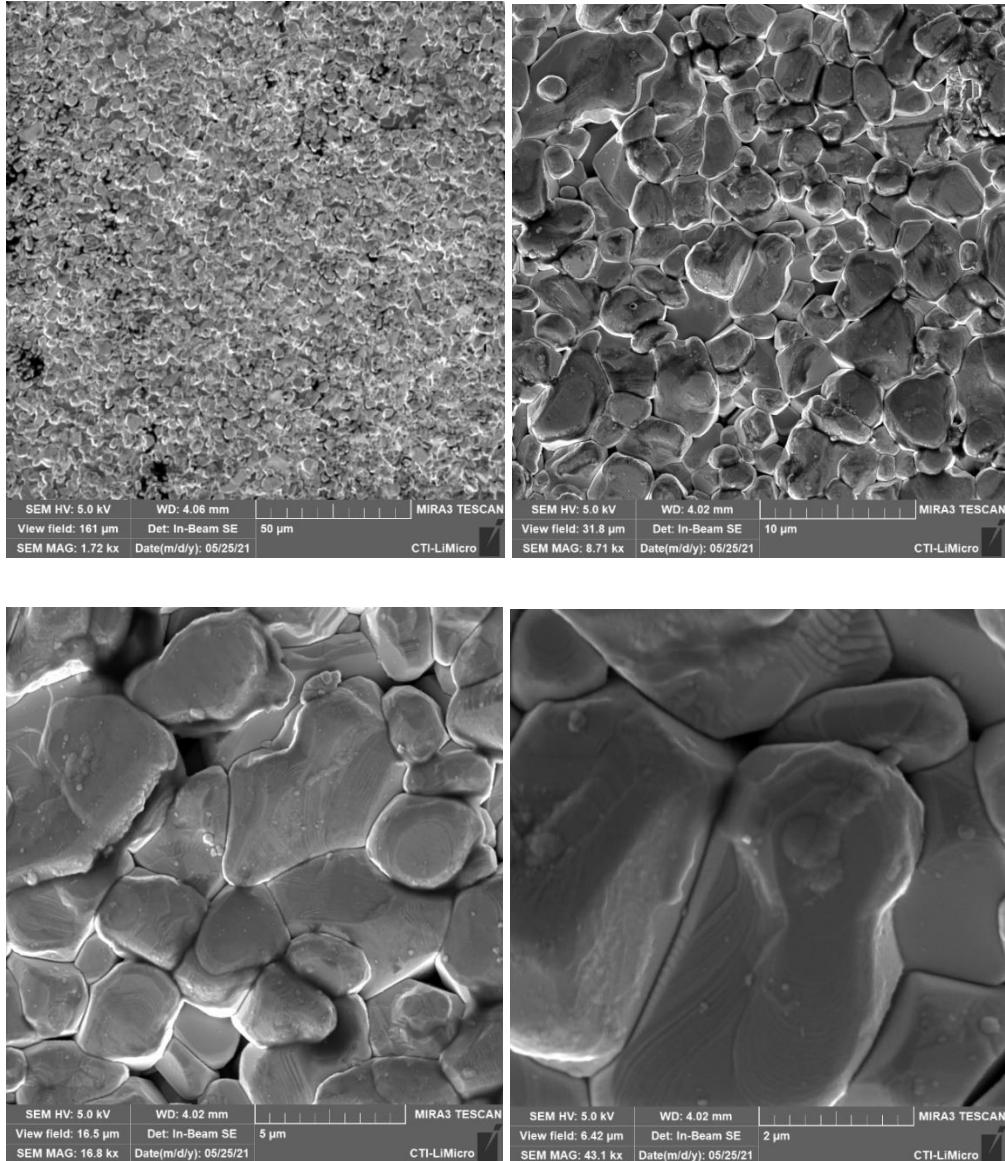


Annx



Annx1: Scanning Electron Microscopy of the TaN film surface varying the magnification.

Table 1: Parameters calculated and extracted from the CxV and IxV curves of the MOS capacitors with TaN/TiO₂ deposited by RF/ALD sputtering, with a thickness of 2 nm of TaN. Flat band voltage (V_{FB}), hysteresis (ΔV_{FB}), Maximum capacitance ($C_{máx}$), Minimum capacitance ($C_{mín}$), Effective charge density (Q_0/q) and Leakage current density in accumulation and inversion.

TaN - 2 nm - square							
Top electrode size	V_{FB}	ΔV_{FB}	$C_{máx}$	$C_{mín}$	Q_0/q	Leakage current in +2V (accumulation)	Leakage current in -2V

							(inversion)
μm	Volts	Volts	Faraday	Faraday	(/cm $^{-2}$)	j(A/cm 2)	j(A/cm 2)
800	1,24	0,02	3,5E $^{-4}$	9,9E $^{-5}$	- 4,23E 17	8E $^{-2}$	-9,2E $^{-6}$
400	1,72	0,13	1,42E $^{-4}$	2,45E $^{-5}$	- 9,54E 17	7,5E $^{-2}$	-7,3E $^{-6}$
200	1,85	0,04	8,17E $^{-5}$	6,05E $^{-6}$	- 2,35E 18	8E $^{-2}$	-6,7E $^{-6}$
100	1,90	0,03	3,36E $^{-5}$	1,4E $^{-6}$	- 4,00E 20	7E $^{-2}$	-5,4E $^{-6}$

Table 2: Parameters calculated and extracted from the CxV and IxV curves of the MOS capacitors with TaN/TiO₂ deposited by RF/ALD sputtering, with a thickness of 4 nm of TaN. Flat band voltage (V_{FB}), hysteresis (ΔV_{FB}), Maximum capacitance (C_{máx}), Minimum capacitance (C_{mín}), Effective charge density (Q_o/q) and Leakage current density in accumulation and inversion.

TaN - 4 nm - square							
Top electrode size	V _{FB}	ΔV_{FB}	C _{máx}	C _{mín}	Q _o /q	Leakage current in +2V (accumulation)	Leakage current in -2V (inversion)
μm	Volts	Volts	Faraday	Faraday	(/cm $^{-2}$)	j(A/cm 2)	j(A/cm 2)
800	1,4	0,01	3E $^{-4}$	8,2E $^{-5}$	-4,04E 17	1,5E $^{-1}$	-3,3E $^{-2}$
400	1,8	0,01	1E $^{-4}$	2,0E $^{-5}$	-7,03E 17	9,2E $^{-1}$	-4,2E $^{-1}$
200	2,04	0,01	4E $^{-5}$	5,0E $^{-6}$	-1,27E 18	9,4E $^{-2}$	-8,5E $^{-4}$
100	2,08	0,01	8E $^{-6}$	1,2E $^{-6}$	-1,01E 20	9E $^{-2}$	-6,4E $^{-4}$